MITSUBISHI ELECTRIC

<IGBT Modules>

CM200TX-13T/CM200TXP-13T

HIGH POWER SWITCHING USE
INSULATED TYPE

TX

Collector current I_C .... **200** A
Collector-emitter voltage V_{CES} .... **650** V
Maximum junction temperature T_{vjmax} .... **175** °C

- ●Flat base type
- ●Copper base plate (Nickel-plating)
- ●RoHS Directive compliant
- ●Tin-plating pin terminals

TXP

Collector current I_C .... **200** A
Collector-emitter voltage V_{CES} .... **650** V
Maximum junction temperature T_{vjmax} .... **175** °C

- ●Flat base type
- ●Copper base plate (Nickel-plating)
- ●RoHS Directive compliant
- ●Tin-plating pressfit terminals

sixpack (three-phase bridge)

●UL Recognized under UL1557, File No. E323585

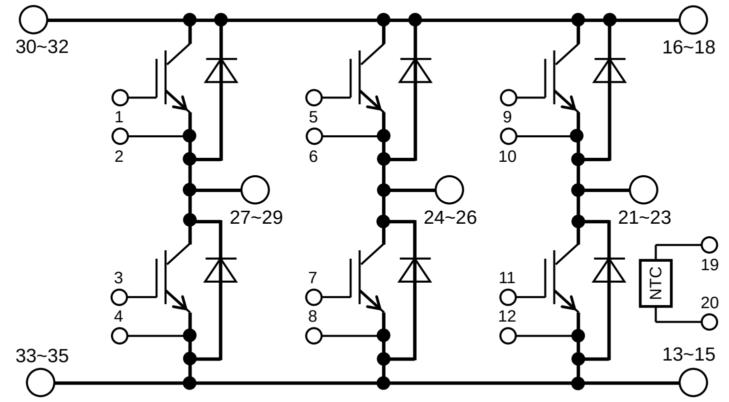
APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

OPTION (Below options are available.)

●PC-TIM (Phase Change Thermal Interface Material) pre-apply

INTERNAL CONNECTION

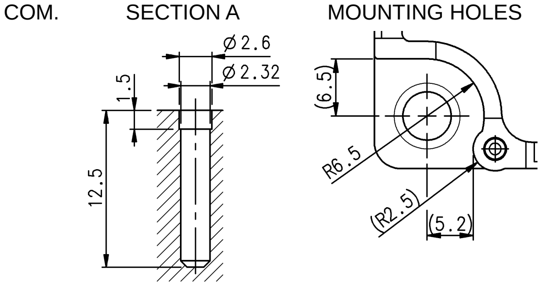


Terminal code

1	GUP	13	N1	24	V
2	EUP	14	N1	25	V
3	GUN	15	N1	26	V
4	EUN	16	P1	27	U
5	GVP	17	P1	28	U
6	EVP	18	P1	29	U
7	GVN	19	TH1	30	P
8	EVN	20	TH2	31	P
9	GWP	21	W	32	P
10	EWP	22	W	33	N
11	GWN	23	W	34	N
12	EWN			35	N

OUTLINE DRAWING

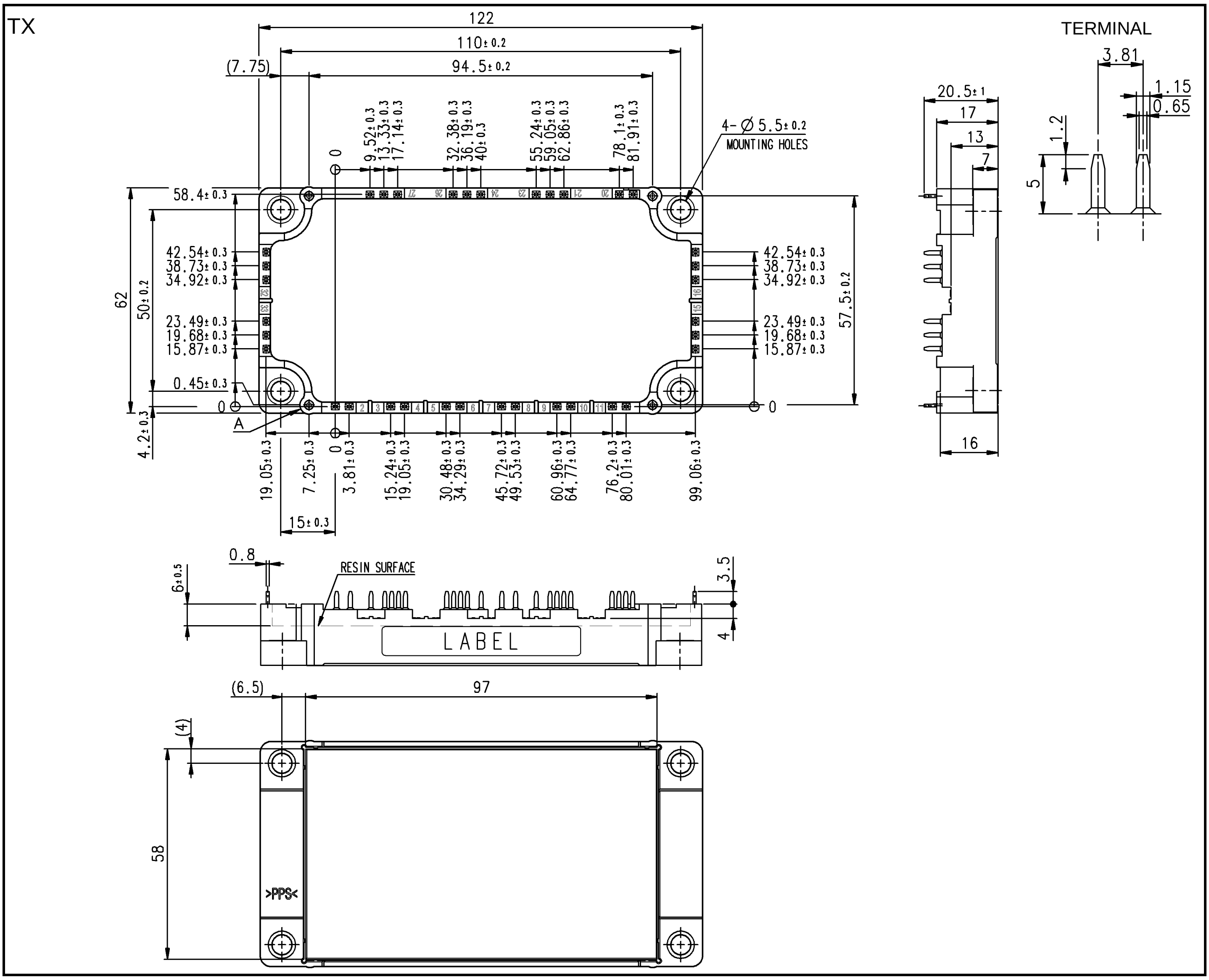
Dimension in mm



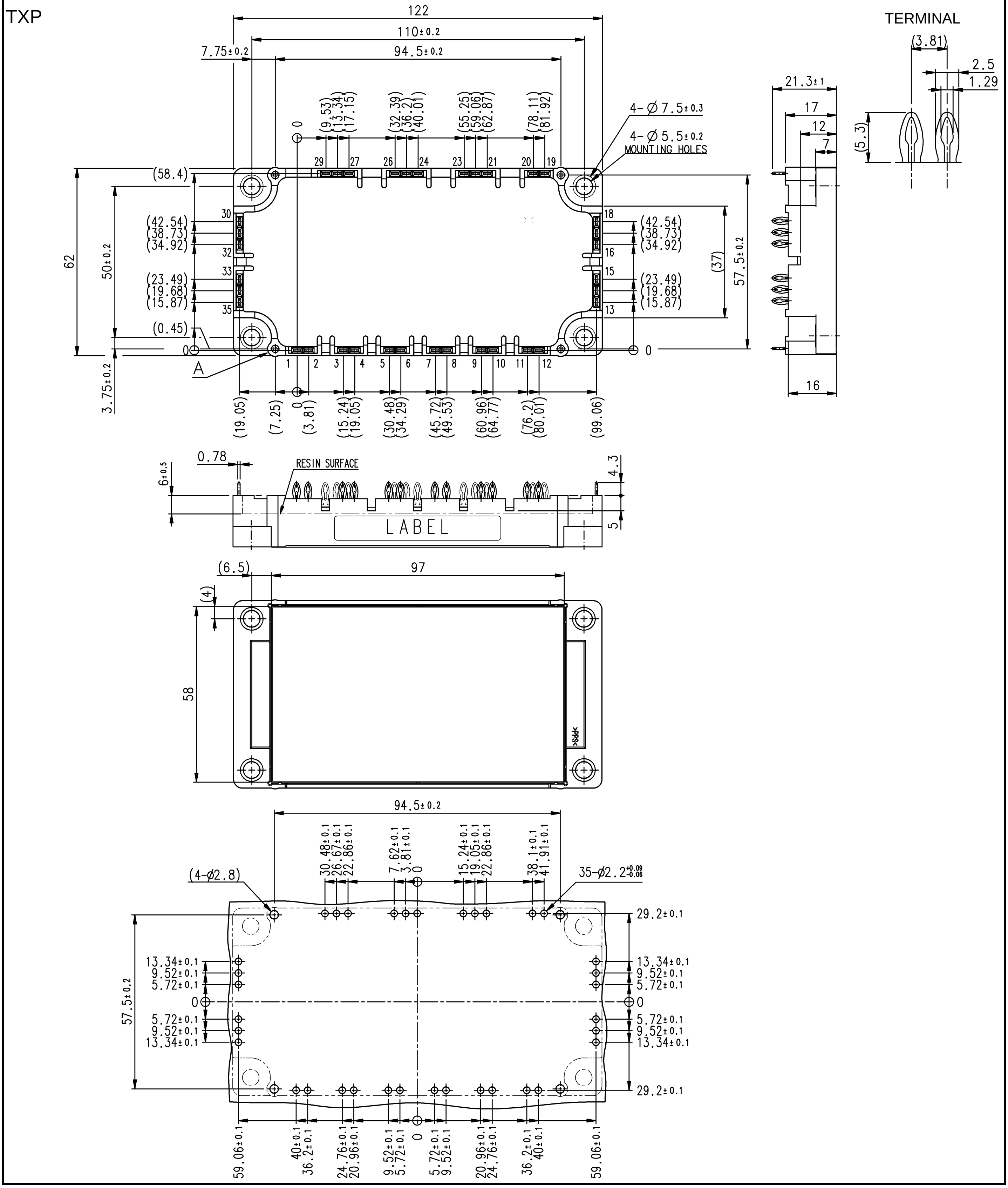
Tolerance otherwise specified

Division of Dimension			Tolerance
	0.5	to 3	±0.2
over	3	to 6	±0.3
over	6	to 30	±0.5
over	30	to 120	±0.8
over	120	to 400	±1.2

OUTLINE DRAWING **Dimension in mm**



OUTLINE DRAWING **Dimension in mm**



MAXIMUM RATINGS (T_{vj}=25 °C, unless otherwise specified)

INVERTER PART IGBT/FWD

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	650	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, T_C=101 °C (Note2, 4)	200	A
I_{CRM}		Pulse, Repetitive (Note3)	400	
P_{tot}	Total power dissipation	T_C=25 °C (Note2, 4)	690	W
I_E (Note1)	Emitter current	DC (Note2)	200	A
I_{ERM} (Note1)		Pulse, Repetitive (Note3)	400	

MODULE

Symbol	Item	Conditions	Rating	Unit
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V
T_{vjmax}	Maximum junction temperature	Instantaneous event (overload)	175	°C
T_{Cmax}	Maximum case temperature	(Note4)	125	
T_{vjop}	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	°C
T_{stg}	Storage temperature	-	-40 ~ +125	

ELECTRICAL CHARACTERISTICS (T_{vj}=25 °C, unless otherwise specified)

INVERTER PART IGBT/FWD

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	V_{CE}=V_{CES}, G-E short-circuited		-	-	1.0	mA
I_{GES}	Gate-emitter leakage current	V_{GE}=V_{GES}, C-E short-circuited		-	-	0.5	μA
$V_{GE(th)}$	Gate-emitter threshold voltage	I_C=20 mA, V_{CE}=10 V		5.4	6.0	6.6	V
V_{CEsat} (Terminal)	Collector-emitter saturation voltage	I_C=200 A, V_{GE}=15 V, Refer to the figure of test circuit (Note5)	T_{vj}=25 °C	-	1.40	1.75	V
			T_{vj}=125 °C	-	1.50	-	
			T_{vj}=150 °C	-	1.55	-	
V_{CEsat} (Chip)		I_C=200 A, V_{GE}=15 V, (Note5)	T_{vj}=25 °C	-	1.30	1.55	V
			T_{vj}=125 °C	-	1.35	-	
			T_{vj}=150 °C	-	1.35	-	
C_{ies}	Input capacitance	V_{CE}=10 V, G-E short-circuited		-	-	26.7	nF
C_{oes}	Output capacitance			-	-	1.1	
C_{res}	Reverse transfer capacitance			-	-	0.5	
Q_G	Gate charge	V_{CC}=300 V, I_C=200 A, V_{GE}=15 V		-	0.83	-	μC
$t_{d(on)}$	Turn-on delay time	V_{CC}=300 V, I_C=200 A, V_{GE}=±15 V, R_G=0.47 Ω, Inductive load		-	-	400	ns
t_r	Rise time			-	-	200	
$t_{d(off)}$	Turn-off delay time			-	-	400	
t_f	Fall time			-	-	600	
V_{EC} (Note1) (Terminal)	Emitter-collector voltage	I_E=200 A, G-E short-circuited, Refer to the figure of test circuit (Note5)	T_{vj}=25 °C	-	1.50	2.05	V
			T_{vj}=125 °C	-	1.55	-	
			T_{vj}=150 °C	-	1.55	-	
V_{EC} (Note1) (Chip)		I_E=200 A, G-E short-circuited, (Note5)	T_{vj}=25 °C	-	1.45	1.85	V
			T_{vj}=125 °C	-	1.50	-	
			T_{vj}=150 °C	-	1.50	-	
t_{rr} (Note1)	Reverse recovery time	V_{CC}=300 V, I_E=200 A, V_{GE}=±15 V, R_G=0.47 Ω, Inductive load		-	-	400	ns
Q_{rr} (Note1)	Reverse recovery charge			-	14	-	μC
E_{on}	Turn-on switching energy per pulse	V_{CC}=300 V, I_C=I_E=200 A, V_{GE}=±15 V, R_G=0.47 Ω, T_{vj}=150 °C, Inductive load		-	3.9	-	mJ
E_{off}	Turn-off switching energy per pulse			-	11.6	-	
E_{rr} (Note1)	Reverse recovery energy per pulse			-	10.1	-	mJ
$R_{CC'+EE'}$	Internal lead resistance	Main terminals-chip, per switch, T_C=25 °C (Note4)		-	1.4	-	mΩ
r_g	Internal gate resistance	Per switch		-	3.0	-	Ω

ELECTRICAL CHARACTERISTICS (cont.; T_{vj}=25 °C, unless otherwise specified)

NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero-power resistance	T_C=25 °C (Note4)	4.85	5.00	5.15	kΩ
ΔR/R	Deviation of resistance	R_{100}=493 Ω, T_C=100 °C (Note4)	-7.3	-	+7.8	%
$B_{(25/50)}$	B-constant	Approximate by equation (Note6)	-	3375	-	K
P_{25}	Power dissipation	T_C=25 °C (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per Inverter IGBT (Note4)		-	-	216	K/kW
$R_{th(j-c)D}$		Junction to case, per Inverter FWD (Note4)		-	-	333	
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1 module,	Thermal grease applied (Note4, 7)	-	11.5	-	K/kW
			PC-TIM applied (Note4, 8)	-	3.1	-	

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
M_s	Mounting torque	Mounting to heat sink	M 5 screw	2.5	3.0	3.5	N·m
d_s	Creepage distance	Solder pin type (TX)	Terminal to terminal	16.4	-	-	mm
			Terminal to base plate	18.5	-	-	
		Pressfit pin type (TXP)	Terminal to terminal	19	-	-	mm
			Terminal to base plate	18.6	-	-	
d_a	Clearance	Solder pin type (TX)	Terminal to terminal	10.2	-	-	mm
			Terminal to base plate	9.0	-	-	
		Pressfit pin type (TXP)	Terminal to terminal	8.9	-	-	mm
			Terminal to base plate	9.0	-	-	
e_c	Flatness of base plate	On the centerline X, Y (Note9)		±0	-	+200	μm
m	mass	-		-	270	-	g

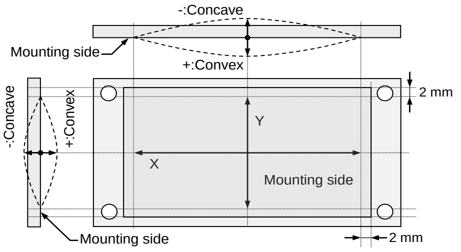
*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

2. Junction temperature (T_{vj}) should not increase beyond T_{vjmax} rating.
3. Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) dose not exceed T_{vjmax} rating.
4. Case temperature (T_C) and heat sink temperature (T_S) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
5. Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
6. $B_{(25/50)}=\ln(\frac{R_{25}}{R_{50}})/(\frac{1}{T_{25}}-\frac{1}{T_{50}})$

   R_{25}: resistance at absolute temperature T_{25} [K]; T_{25}=25 [°C]+273.15=298.15 [K]

   R_{50}: resistance at absolute temperature T_{50} [K]; T_{50}=50 [°C]+273.15=323.15 [K]
7. Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K)/$D_{(C-S)}$=50 μm.
8. Typical value is measured by using PC-TIM of λ=3.4 W/(m·K)/$D_{(C-S)}$=50 μm.
9. The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



Note10. Use the following screws when mounting the printed circuit board (PCB) on the standoffs.
PCB thickness : t=1.6

Type	Manufacturer	Size	Tightening torque (N・m)	Recommended tightening method
(1) PT®	EJOT	K25×8	0.55 ± 0.055	by handwork (equivalent to 30 rpm by mechanical screw driver) ~ 600 rpm (by mechanical screw driver)
(2) PT®		K25×10	0.75 ± 0.075 N・m	
(3) DELTA PT®		25×8	0.55 ± 0.055 N・m	
(4) DELTA PT®		25×10	0.75 ± 0.075 N・m	
(5) B1 tapping screw	-	φ2.6×10	0.75 ± 0.075 N・m	
		φ2.6×12		

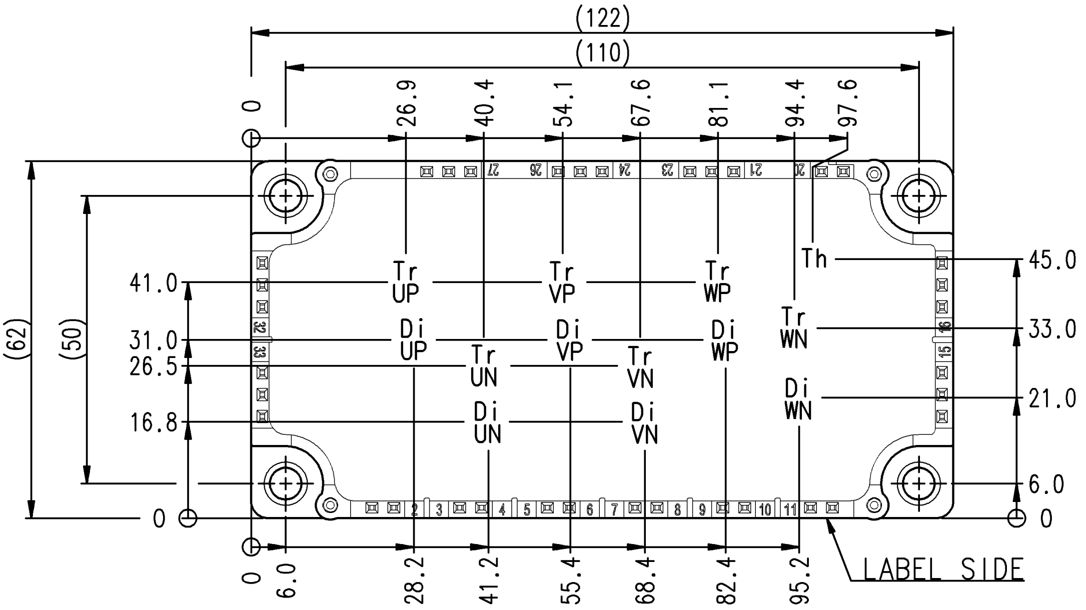
RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across P-N terminals	-	300	450	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G*P-E*P/G*N-E*N terminals (*=U,V,W)	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	0.47	-	30	Ω

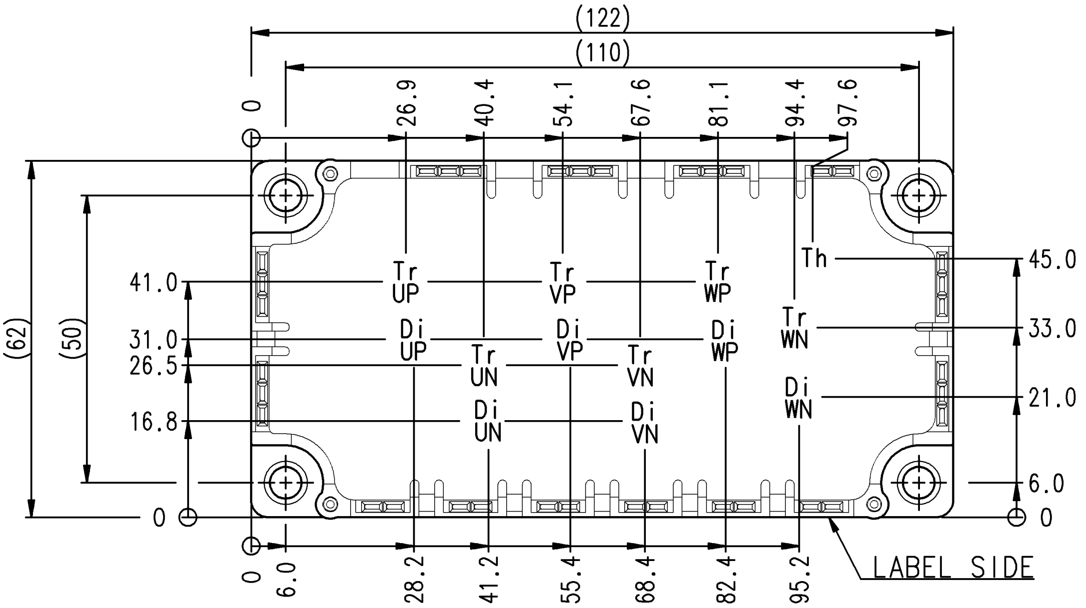
CHIP LOCATION (Top view)

Dimension in mm, tolerance: ±1 mm

TX

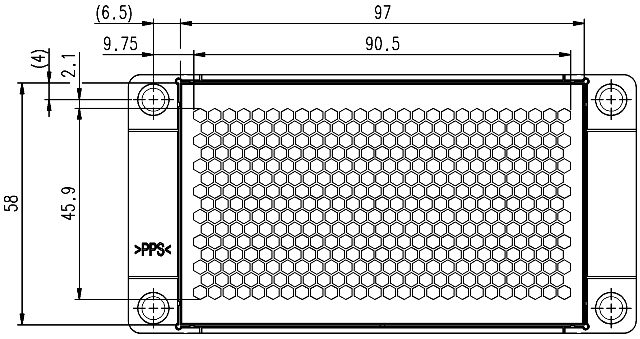
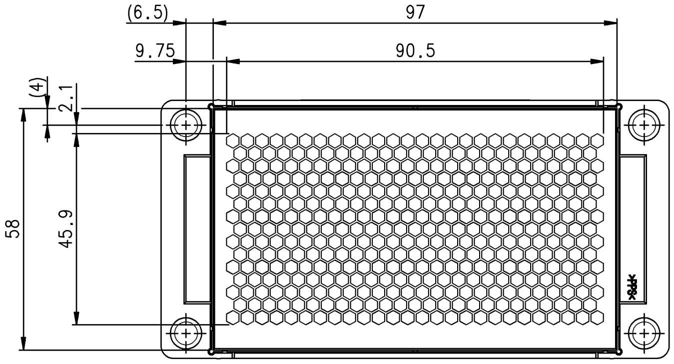


TXP

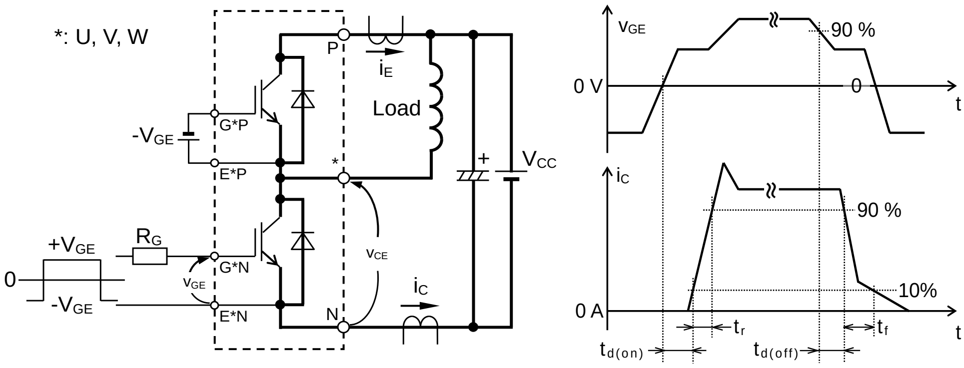


Tr*P/Tr*N: IGBT, Di*P/Di*N: FWD (*=U,V,W), Th: NTC thermistor

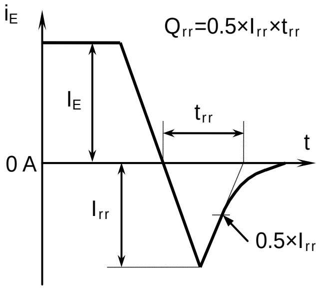
Option: PC-TIM applied baseplate outline

TX	TXP
	

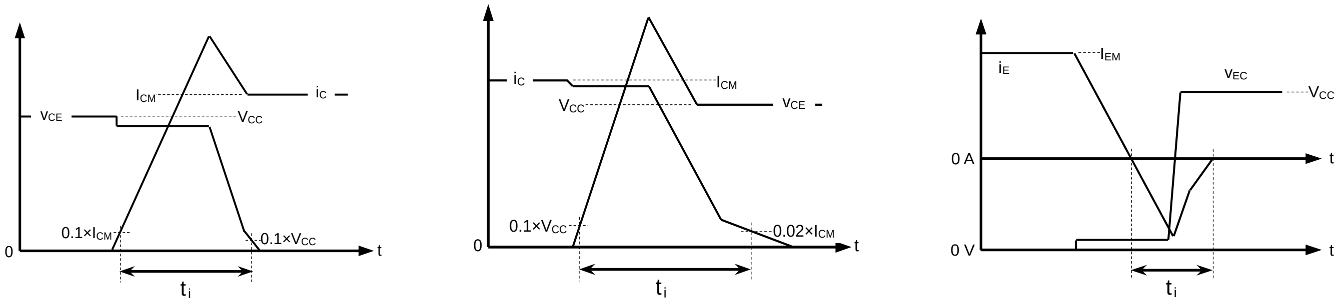
TEST CIRCUIT AND WAVEFORMS



Switching characteristics test circuit and waveforms



t_{rr}, Q_{rr} characteristics test waveform



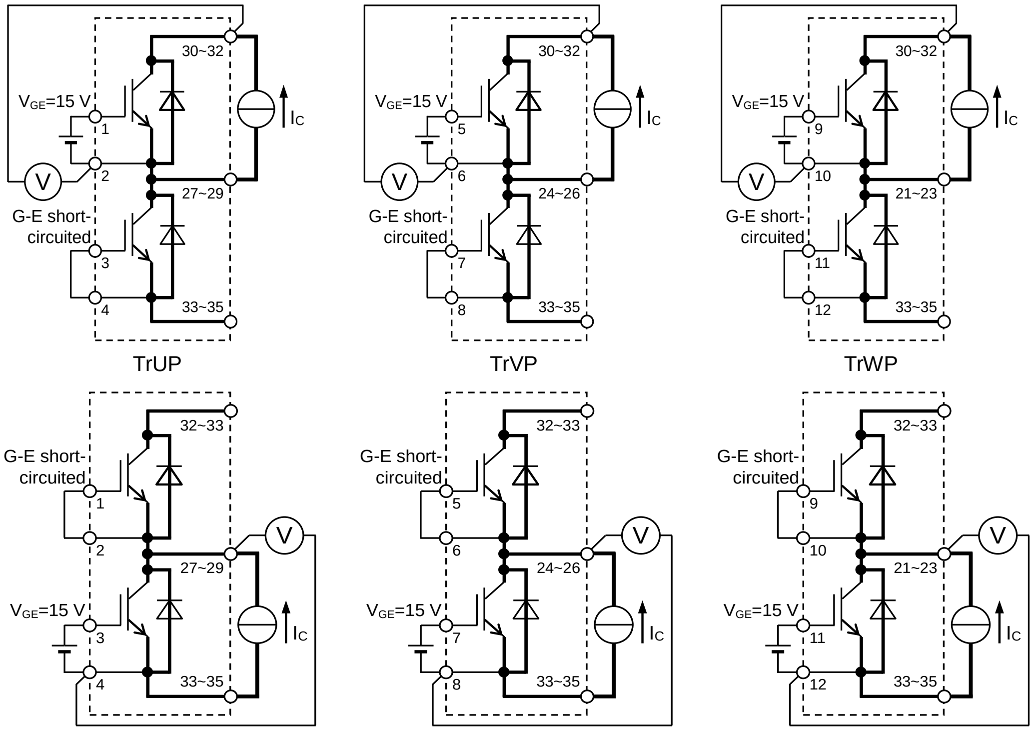
IGBT Turn-on switching energy

IGBT Turn-off switching energy

FWD Reverse recovery energy

Switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT



TrUP TrVP TrWP

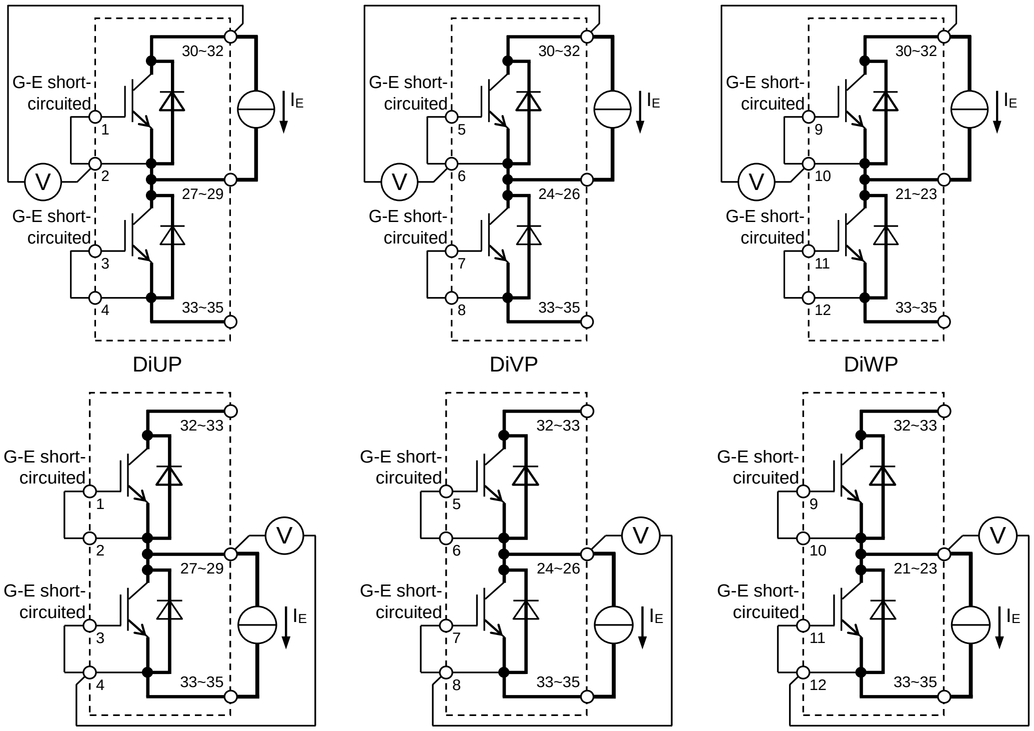
TrUN TrVN TrWN

Gate-emitter short-circuited GVP-EVP, GVN-EVN, GWP-EWP, GWN-EWN

Gate-emitter short-circuited GUP-EUP, GUN-EUN, GWP-EWP, GWN-EWN

Gate-emitter short-circuited GUP-EUP, GUN-EUN, GVP-EVP, GVN-EVN

V_{CEsat} characteristics test circuit



DiUP DiVP DiWP

DiUN DiVN DiWN

Gate-emitter short-circuited GVP-EVP, GVN-EVN, GWP-EWP, GWN-EWN

Gate-emitter short-circuited GUP-EUP, GUN-EUN, GWP-EWP, GWN-EWN

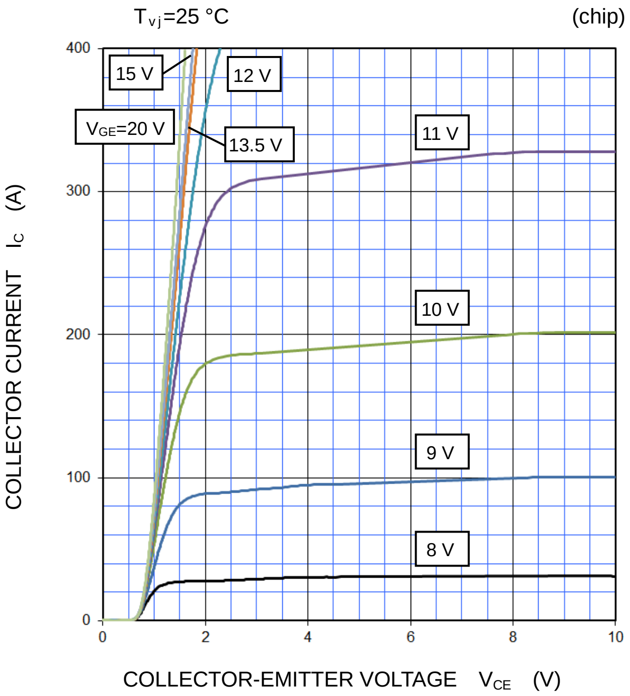
Gate-emitter short-circuited GUP-EUP, GUN-EUN, GVP-EVP, GVN-EVN

V_{EC} characteristics test circuit

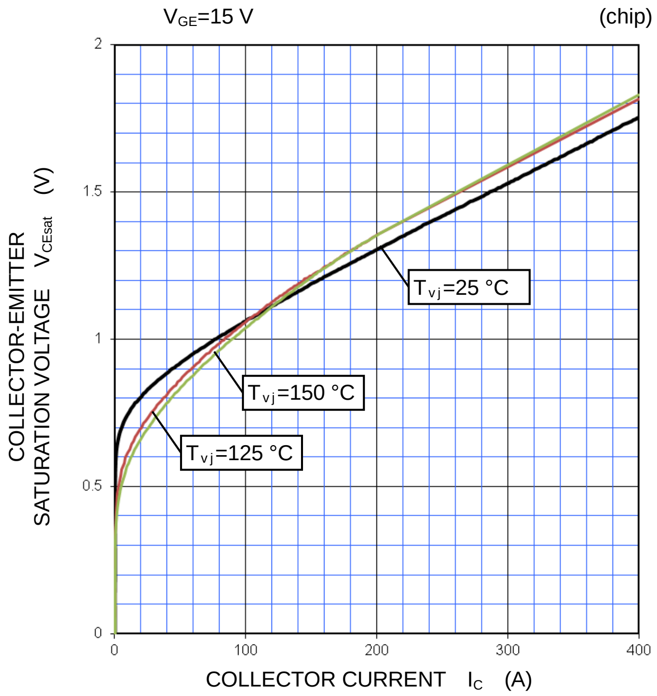
PERFORMANCE CURVES

INVERTER PART

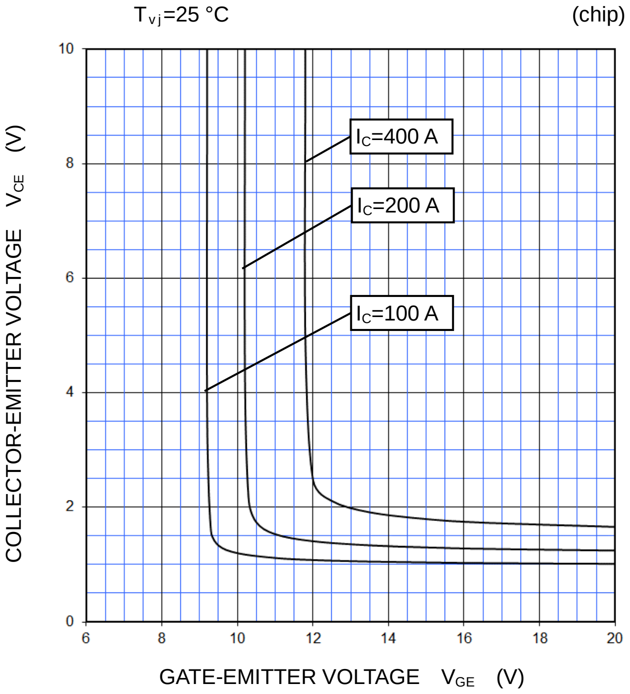
OUTPUT CHARACTERISTICS (TYPICAL)



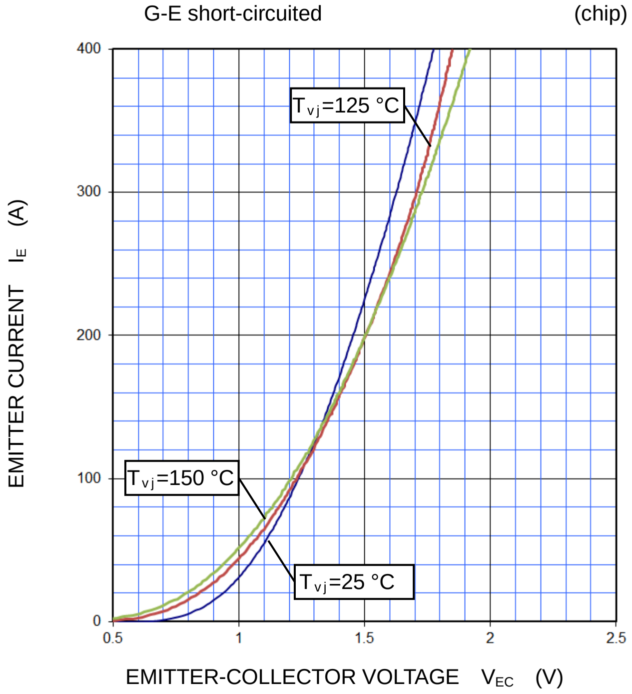
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS (TYPICAL)



FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)

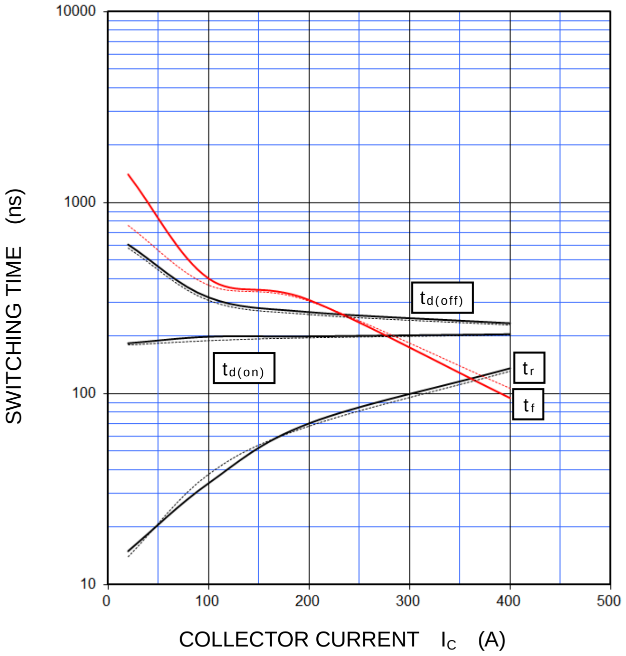


PERFORMANCE CURVES

INVERTER PART

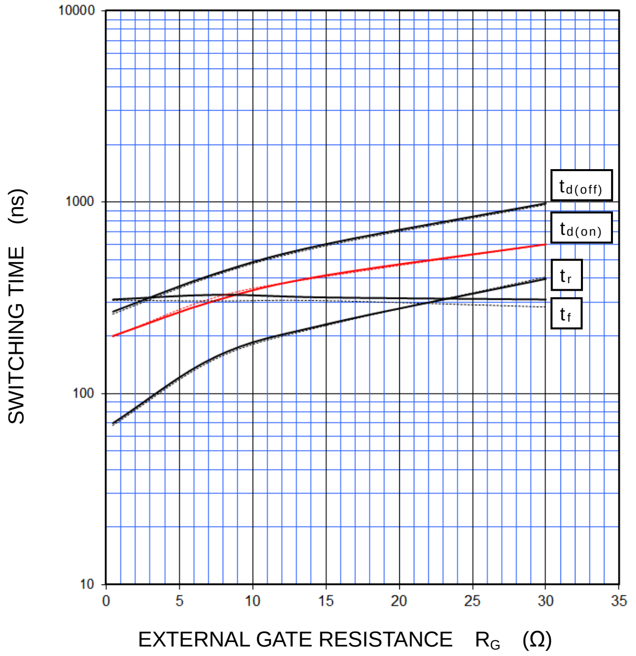
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=300 V, R_G=0.47 Ω, V_{GE}=±15 V, INDUCTIVE LOAD
———: T_{vj}=150 °C, - - - - -: T_{vj}=125 °C



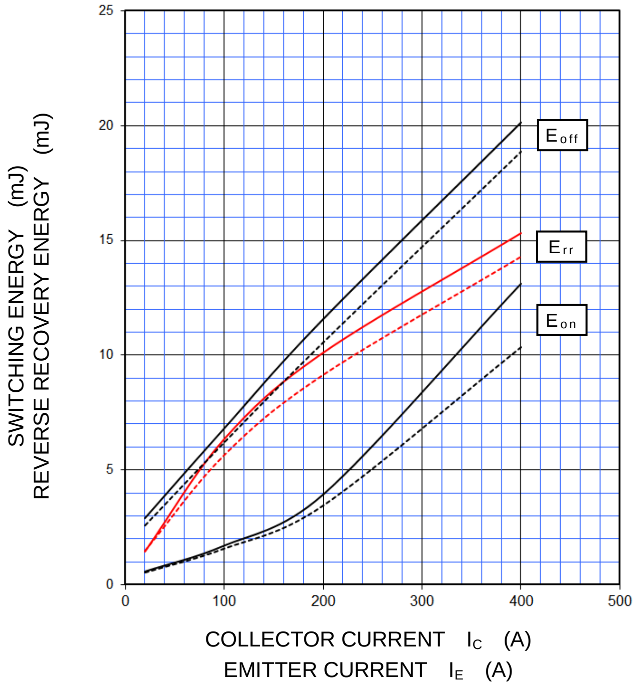
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=300 V, I_C=200 A, V_{GE}=±15 V, INDUCTIVE LOAD
———: T_{vj}=150 °C, - - - - -: T_{vj}=125 °C



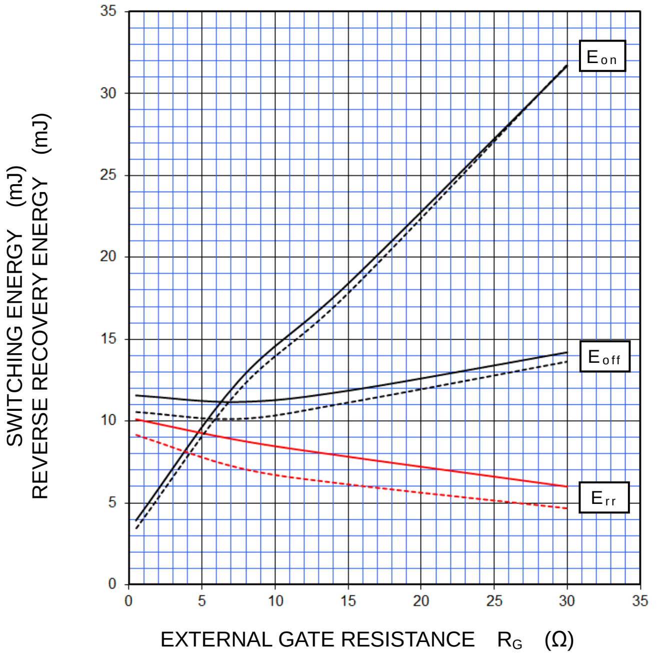
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=300 V, R_G=0.47 Ω, V_{GE}=±15 V, INDUCTIVE LOAD,
———: T_{vj}=150 °C, - - - - -: T_{vj}=125 °C, PER PULSE



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

V_{CC}=300 V, I_C/I_E=200 A, V_{GE}=±15 V, INDUCTIVE LOAD,
———: T_{vj}=150 °C, - - - - -: T_{vj}=125 °C, PER PULSE

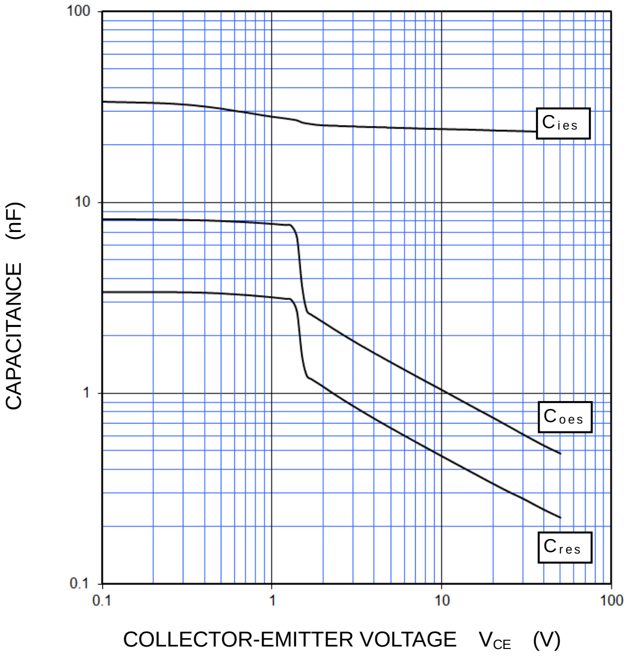


PERFORMANCE CURVES

INVERTER PART

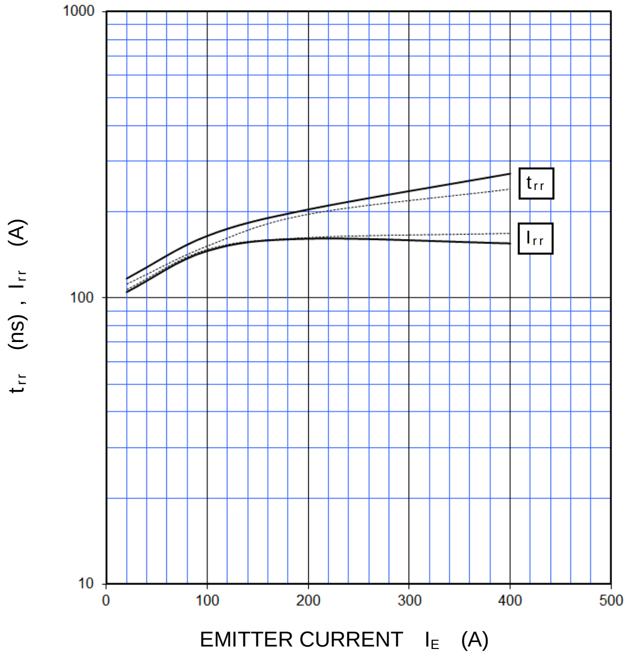
CAPACITANCE CHARACTERISTICS (TYPICAL)

G-E short-circuited, T_{vj}=25 °C



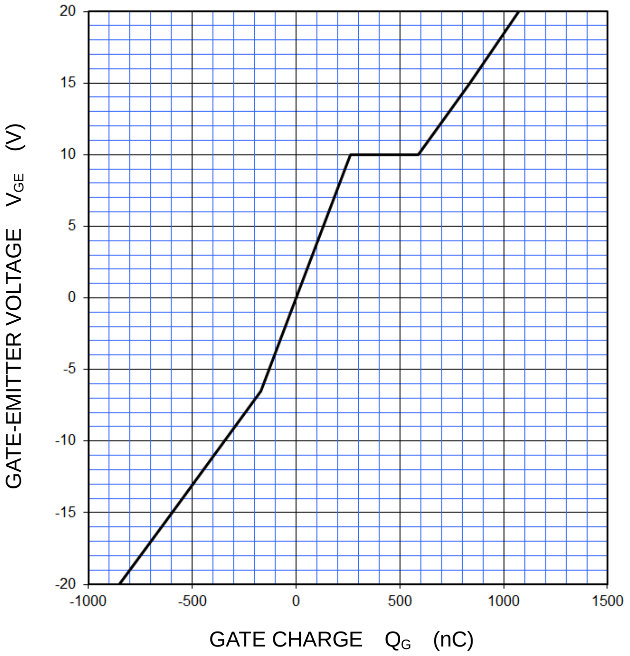
FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

V_{CC}=300 V, R_G=0.47 Ω, V_{GE}=±15 V, INDUCTIVE LOAD
———: T_j=150 °C, - - - - -: T_j=125 °C



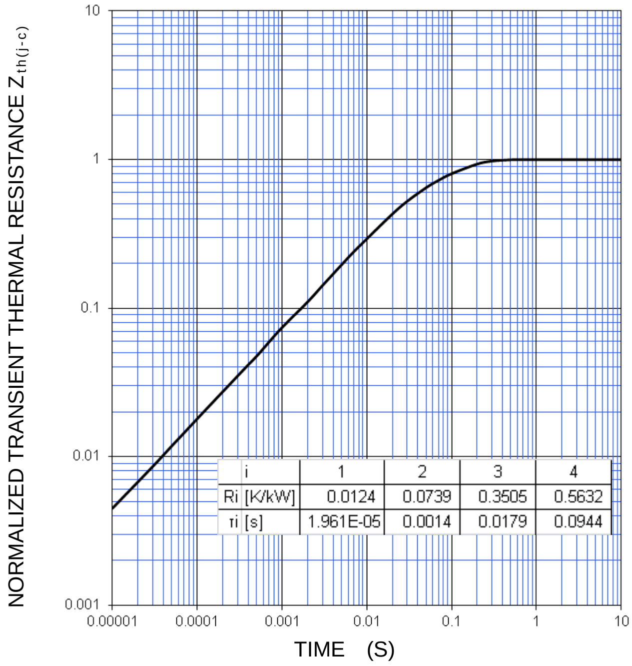
GATE CHARGE CHARACTERISTICS (TYPICAL)

V_{CC}=300 V, I_C=200 A, T_{vj}=25 °C



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

Single pulse, T_C=25 °C
$R_{th(j-c)Q}$=216 K/kW, $R_{th(j-c)D}$=333 K/kW



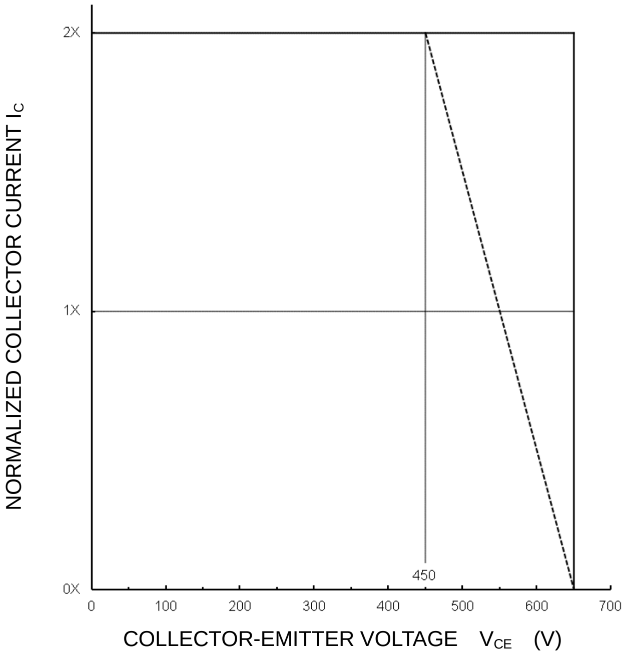
i	1	2	3	4
Ri [K/kW]	0.0124	0.0739	0.3505	0.5632
τi [s]	1.961E-05	0.0014	0.0179	0.0944

PERFORMANCE CURVES

INVERTER PART

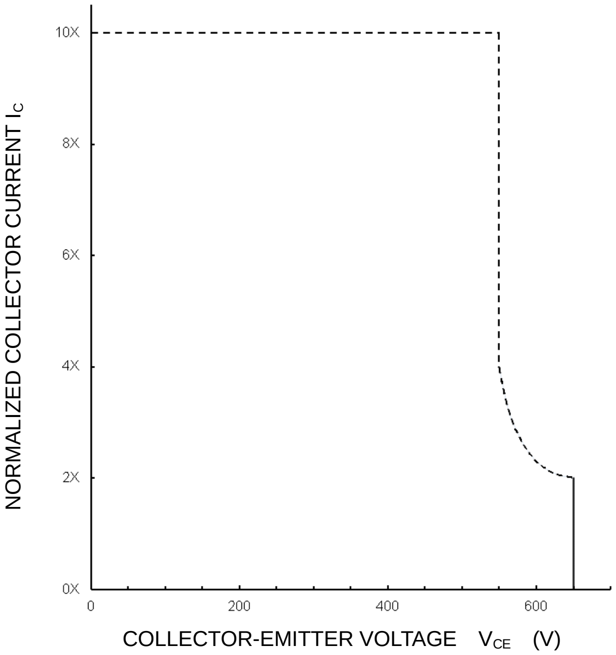
TURN-OFF SWITCHING SAFE OPERATIONG AREA (REVERSE BIAS SAFE OPERATING AREA) (MAXIMUM)

$V_{CC} \leq 450$ V, R_G=0.47~30 Ω, V_{GE}=±15 V,
————: T_{vj}=25~150 °C (Normal load operations (Continuous)
- - - - - -: T_{vj}=175 °C (Unusual load operations (Limited period)



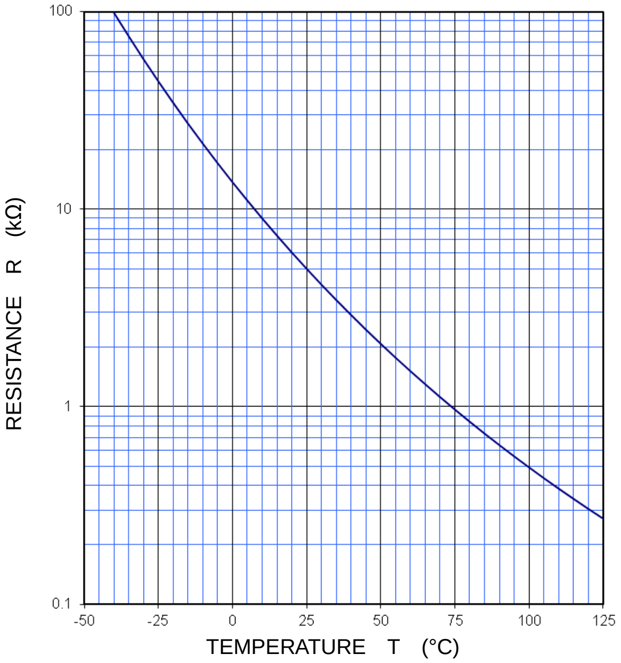
SHORT-CIRCUIT SAFE OPERATING AREA (MAXIMUM)

$V_{CC} \leq 400$ V, R_G=0.47~30 Ω, V_{GE}=±15 V,
T_{vj}= 25 ~ 150 °C, $t_W \leq 8$ μs, Non-Repetitive



NTC thermistor part

TEMPERATURE CHARACTERISTICS (TYPICAL)



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Keep safety first in your circuit designs!

This product is designed for industrial application purpose. The performance, the quality and support level of the product is guaranteed by “Customer's Std. Spec.”.
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